FIG. 1A (PRIOR ART)

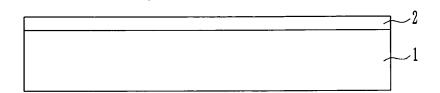


FIG. 1B (PRIOR ART)

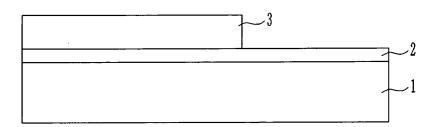


FIG. 1C (PRIOR ART)

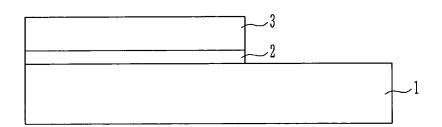


FIG. 1D (PRIOR ART)

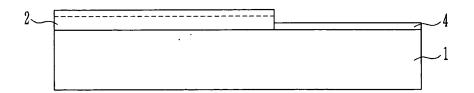


FIG. 2 (PRIOR ART)

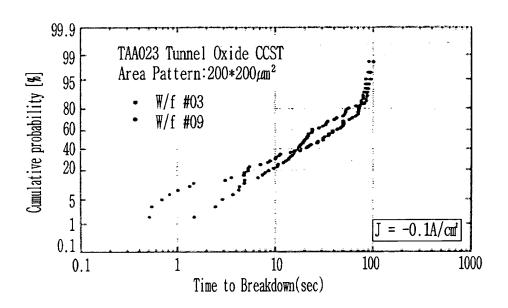
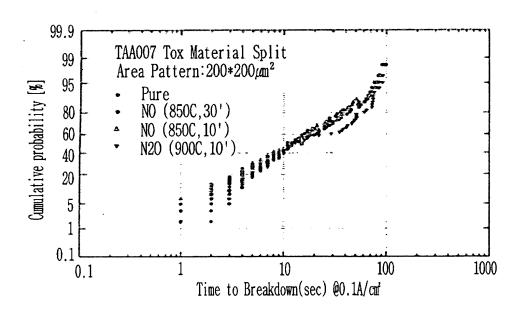


FIG. 3 (PRIOR ART)



29936/39868
Seung Cheol Lee and Sang Wook Park
METHOD OF FORMING TUNNEL OXIDE
FILM IN SEMICONDUCTOR DEVICE
Sheet 3 of 4

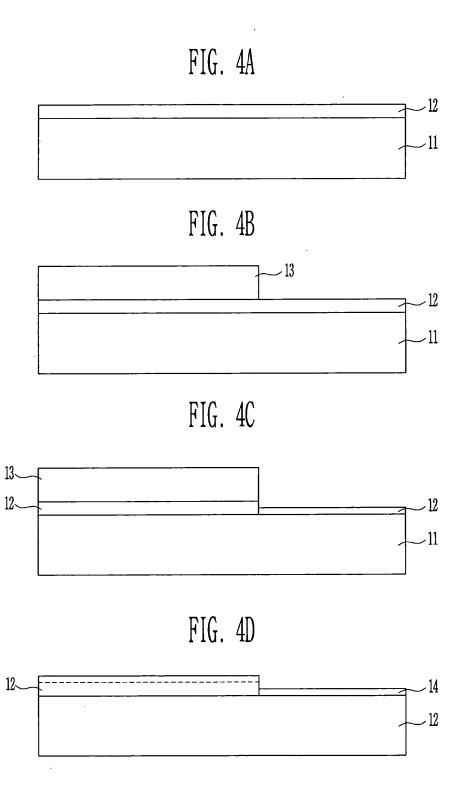


FIG. 5

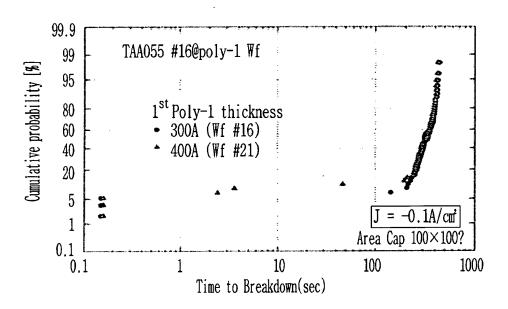


FIG. 6

		208	278	427	263	285		
	352	430	424	228	462	273	394	
317	369	336	234	215	309	404	390	321
07	440	311	301	387	306	269	368	425
0	401	306	354	282	313	492	419	403
000	315	398	390	251	463	397	289	267
	311	448	314	457	294	294	253	
		144	386	377	447	396		